IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Darrell Rinerson et al. Attorney Docket No.: UNTYP038

Application No.: New Examiner: Not Yet Assigned

Filed: Herewith Group: Not Yet Assigned

Title: MULTI-RESISTIVE STATE ELEMENT Confirmation No.: Not Yet Assigned

WITH REACTIVE METAL

CERTIFICATE OF EXPRESS MAILING

I hereby certify that this paper and the documents and/or fees referred to as attached therein are being deposited with the United States Postal Service on February 06/2004 in an envelope as "Express Mail Post Office to Addressee" service under 37 CFR §1.10, Mailing Label Number EV/33986709US, addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

Aurelia Sanchez

INFORMATION DISCLOSURE STATEMENT 37 CFR §§1.56 AND 1.97(b)

Mail Stop Patent Application Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, copies of which are enclosed**, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure

^{**} Copies of U.S. Patents and U.S. Published Applications are not enclosed.

Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. UNTYP038).

Respectfully submitted,

BEYER WEAVER & THOMAS, LLP

Morgan E. Malino Registration No. 41,177

P.O. Box 778 Berkeley, CA 94704-0778 (650) 961-8300

Form 1449 (Modified)	Atty Docket No.	Application No.:
	UNTYP038	New
Information Disclosure	Applicant:	
Statement By Applicant	Rinerson et al.	
	Filing Date	Group
(Use Several Sheets if Necessary)	Herewith	Not Yet Assigned

U.S. Patent Documents

Examiner						Sub-	Filing
Initial	No.	Patent No.	Date	Patentee	Class	class	Date
*	Α	6,204,139	03/20/01	Liu, et al.	438	385	8/25/1998
*	В	6,531,371	03/11/03	Hsu et al.	438	385	6/28/2001

Other Documents

Initial No. Author, Title, Date, Place (e.g. Journal) of Publication C Beck, A. et al., "Reproducible switching effect in thin oxide films for memorapplications," Applied Physics Letters, Vol. 77, No. 1, 3 July 2000,139-14 D Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651. E Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Puls Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages F Rossel, C. et al., "Electrical current distribution across a metal-insulator-			Control of the contro	
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Examiner Date Considered		G	nonvolatile memory in chromium-doped SrTiO ₃ single crystals," Applied	
	Examiner	1	Date Considered	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.